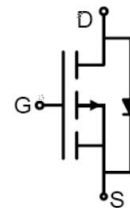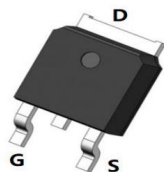|	
V_{DSS}	-20V
R_{DS}( )	5 (.)
I_D	-60A

A a c MOSFET c c
S ca PWM, a c a
a a ca
U a - a c a c a
Fa c a b c
150 a a

I a c c ac c a c - a c
a a a c a .T a c b a a c a ab
c c a ca a a a a ca .

I_D @ T_C = 25 C	C D a C , V_{GS} @ 10V	-60	A
I_D @ T_C = 100 C	C D a C , V_{GS} @ 10V	-39	
I_{DM}	P D a C	-240	
P_D @T_C = 25 C	P D a	60	W
V_{DS}	D a -S c V a	-20	V
V_{GS}	Ga - -S c V a	12	V
E_{AS}	S P A a a c E @ L=0.5 H	40	J
T_J T_{STG}	O a J c a S a T a Ra	-55 +150	C

R JC	J c - -Ca		2.1	/W

@T$_A$=25　　　　　c

		Min	Typ	Max	Unit	Conditions
V$_{(BR)DSS}$	D a - -S c b a a	-20			V	V$_{GS}$ = 0V, I$_D$ = -250 A
R$_{DS()}$	S a c D a - -S c - a c		5	6.5		V$_{GS}$= -4.5V, I$_D$ = -15A
			7	9		V$_{GS}$= -2.5V, I$_D$ = -12A
V$_{GS()}$	Ga a	-0.4		-1	V	V$_{DS}$ = V$_{GS}$, I$_D$ = -250 A
I$_{DSS}$	D a - -S c a a c			-1	A	V$_{DS}$ = -20V, V$_{GS}$ = 0V
I$_{GSS}$	Ga - -S c a a a			100	A	V$_{GS}$ =12V
			-100			V$_{GS}$ = -12V
C	I ca ac a c		3460			V$_{GS}$ = 0V
C	O ca ac a c		545		F	V$_{DS}$ = -10V
C	R a ca ac a c		490			= 1MH
Q	T a a c a		55			I$_D$ = -15A,
Q	Ga - -S c c a		8		C	V$_{DS}$= -4.5V,
Q	Ga - -Da ("M ") c a		15			V$_{GS}$ = -4.5V
( )	T - a		10			
	R		110			V$_{GS}$= -10V, V$_{DD}$ = -10V,
( )	T -O a		155			R$_{GEN}$=2.7 , I$_D$ = -13A
	Fa		160			

I$_S$	C S c C (B D)		-60	A	MOSFET b
I$_{SM}$	P S c C (B D)		-240	A	a - c .
V$_{SD}$	D F a V a		-1.2	V	I$_S$=-30A, V$_{GS}$=0V
	R R c T	18			T$_J$ = 25 C, I$_F$ =-15A, / =
Q	R R c C a	7.7		C	100A/
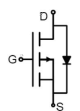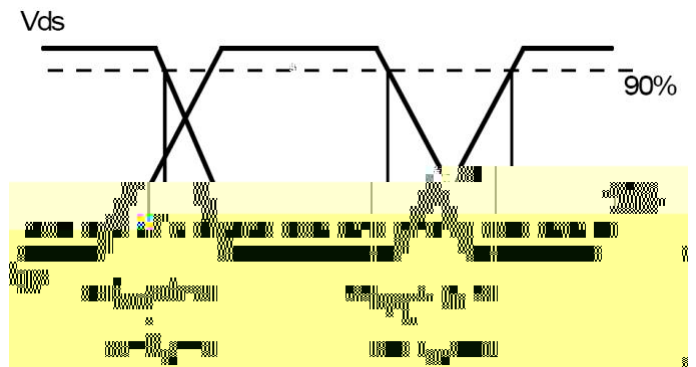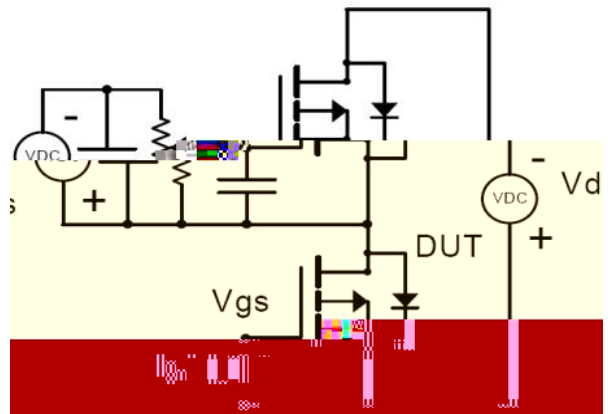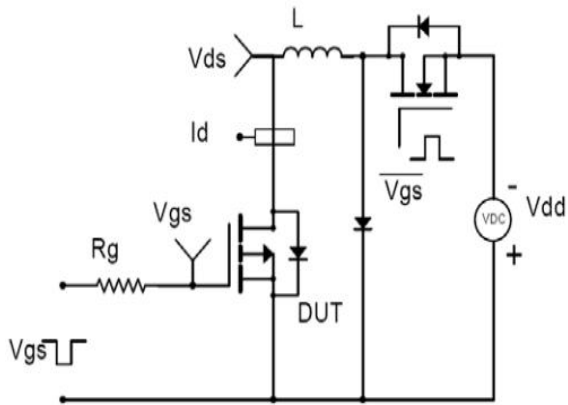
Ca c a   c   c   ba   a   a ab c   a   .
R   a ;   b a . c   a   .
T   a PD ba   a . c   a   ,   c - -ca   a
     a c .
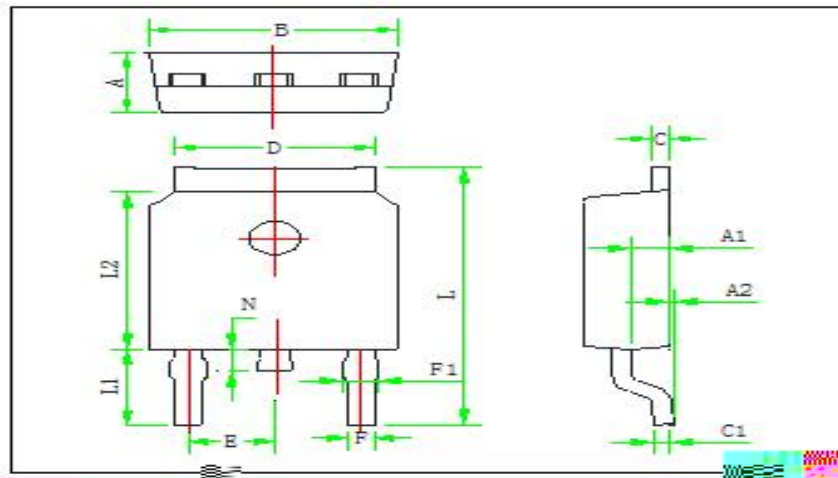
Symbol	Min	Typ	Max
A	2.20	2.30	2.40
A1	0.91	1.01	1.11
A2	0.05	0.15	0.25
B	6.45	6.60	6.75
C	0.45	0.50	0.58
C1	0.45	0.50	0.58
D	5.12	5.32	5.52
E		2.286 TYP	
F	0.66	0.76	0.86
F1	0.66	0.86	1.06
L	9.60	9.90	10.20
L1	2.6	2.8	3.0
L2	5.95	6.10	6.25
N	0.60	0.80	1.00

A a aS   c   c b   c a   a   c ca   a ca a